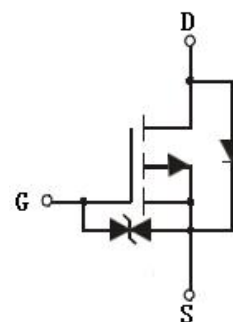
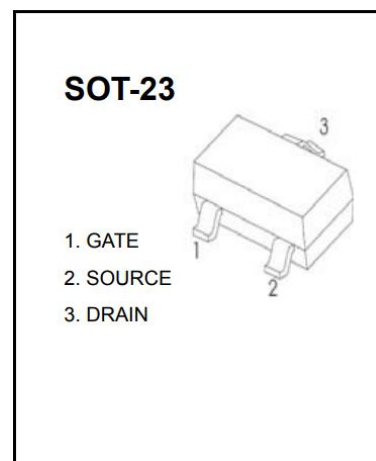


Plastic-Encapsulate MOSFETS

P-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Lead Free By Design/RoHS Compliant (Note 2)
- ESD Protected Up To 2kV
- MARKING: PA1



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-20	V
Gate-Source Voltage			V _{GSS}	±6	V
Drain Current (Note 1)	Steady State	T _A = 25°C	I _D	-0.46	A
		T _A = 85°C		-0.33	
Pulsed Drain Current			I _{DM}	-6	A

Thermal Characteristics @T_A = 25°C unless otherwise specified

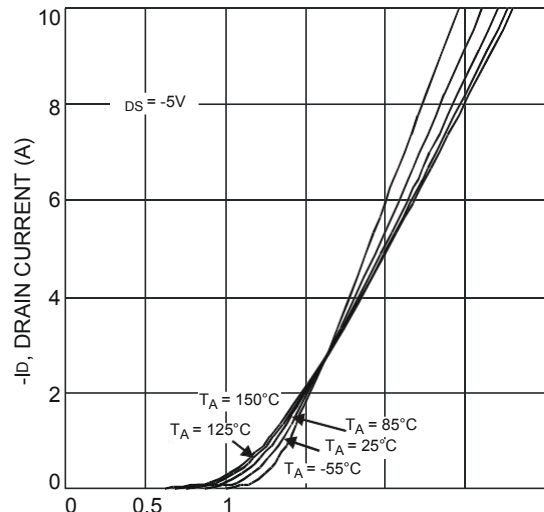
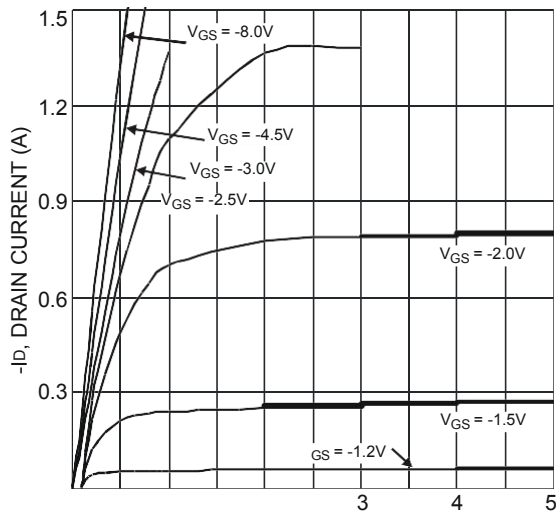
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 1)		P _D	0.27	W
Thermal Resistance, Junction to Ambient		R _{θJA}	461	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Notes: 1. Device mounted on FR-4 PCB.
2. No purposefully added lead.

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = 25°C	I _{DSS}	-	-	-100	nA	V _{DS} = -20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±2.0	μA	V _{GS} = ±4.5V, V _{DS} = 0V
ON CHARACTERISTICS (Note 4)						
Gate Threshold Voltage	V _{GS(th)}	-0.5	-	-1.0	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	0.8	0.9	Ω	V _{GS} = -4.5V, I _D = -350mA
			0.9	1.05		V _{GS} = -2.5V, I _D = -300mA
			1.5	1.7		V _{GS} = -1.8V, I _D = -150mA
Forward Transfer Admittance	Y _{fs}	-	0.9	-	S	V _{DS} = -10V, I _D = -250mA
Diode Forward Voltage (Note 4)	V _{SD}	-	-0.8	-1.2	V	V _{GS} = 0V, I _S = -150mA
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	-	59.76	-	pF	V _{DS} = -16V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	12.07	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	6.36	-	pF	
Total Gate Charge	Q _g	-	622.4	-	pC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -250mA
Gate-Source Charge	Q _{gs}	-	100.3	-	pC	
Gate-Drain Charge	Q _{gd}	-	132.2	-	pC	
Turn-On Delay Time	t _{D(on)}	-	5.1	-	ns	V _{DD} = -10V, V _{GS} = -4.5V, R _L = 47Ω, R _G = 10Ω, I _D = -200mA
Turn-On Rise Time	t _r	-	8.1	-	ns	
Turn-Off Delay Time	t _{D(off)}	-	28.4	-	ns	
Turn-Off Fall Time	t _f	-	20.7	-	ns	

Notes: 4. Short duration pulse test used to minimize self-heating effect.



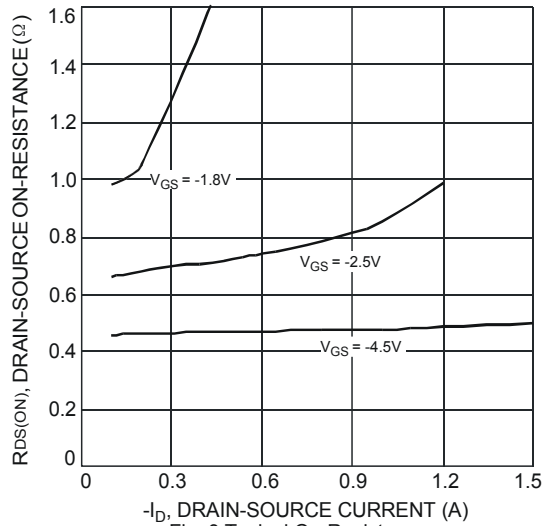


Fig. 3 Typical On-Resistance
vs. Drain Current and Gate Voltage

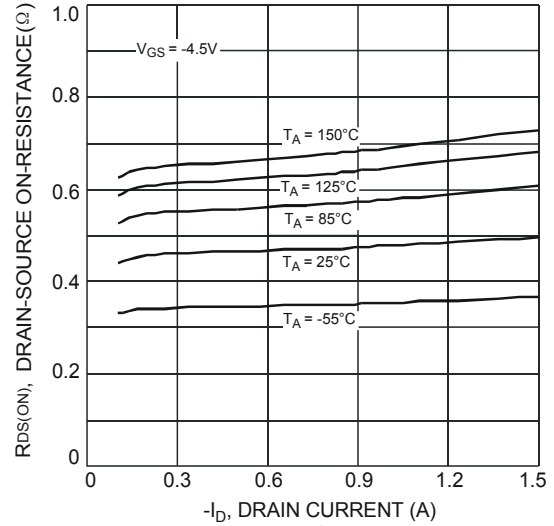


Fig. 4 Typical On-Resistance vs.
Drain Current and Temperature

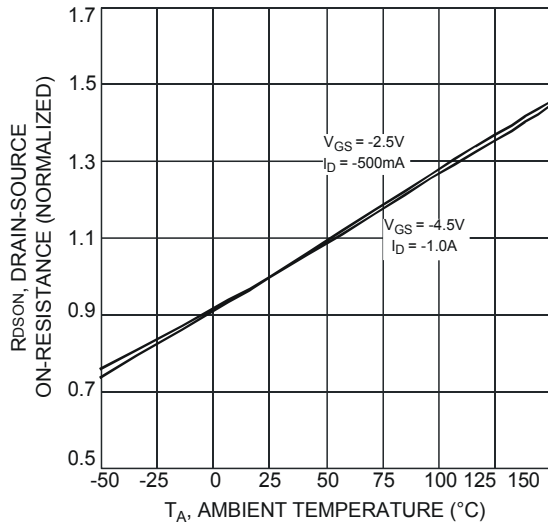


Fig. 5 On-Resistance Variation with Temperature

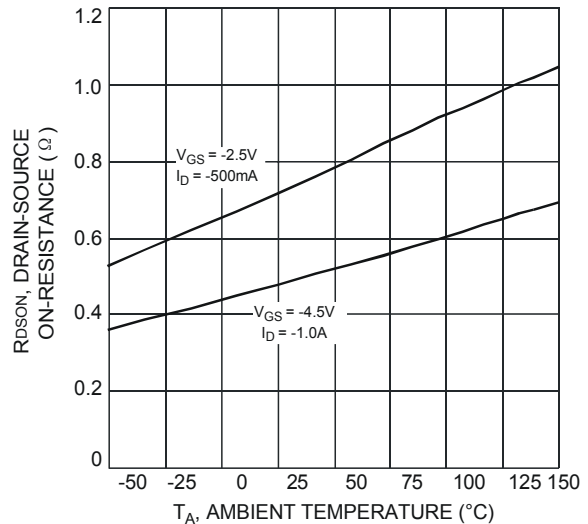


Fig. 6 On-Resistance Variation with Temperature

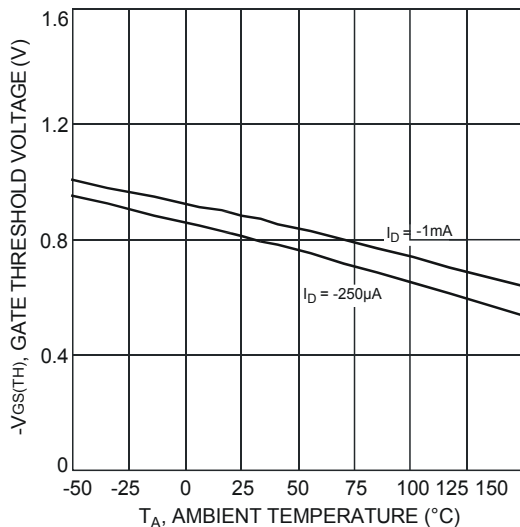


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

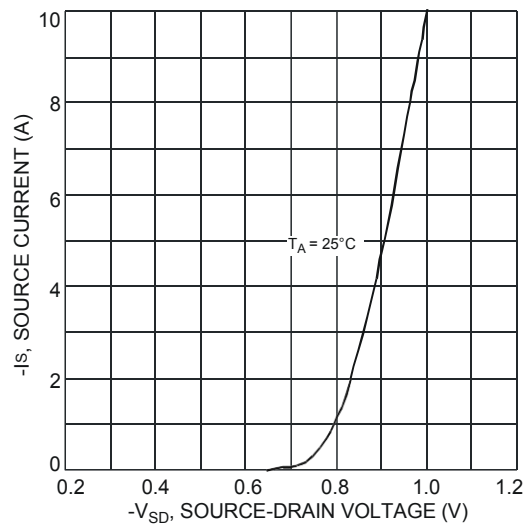


Fig. 8 Diode Forward Voltage vs. Current

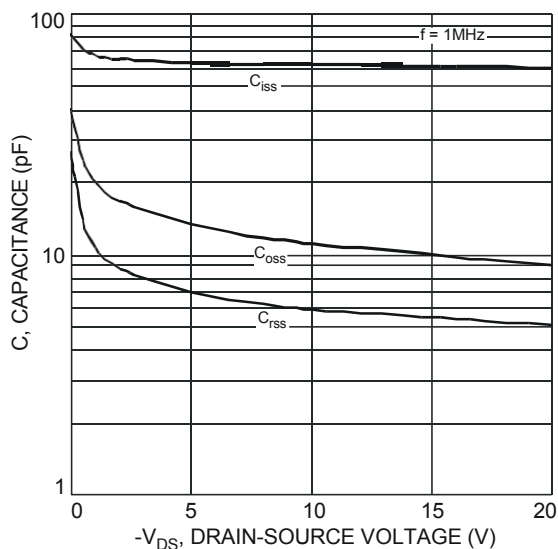


Fig. 9 Typical Total Capacitance

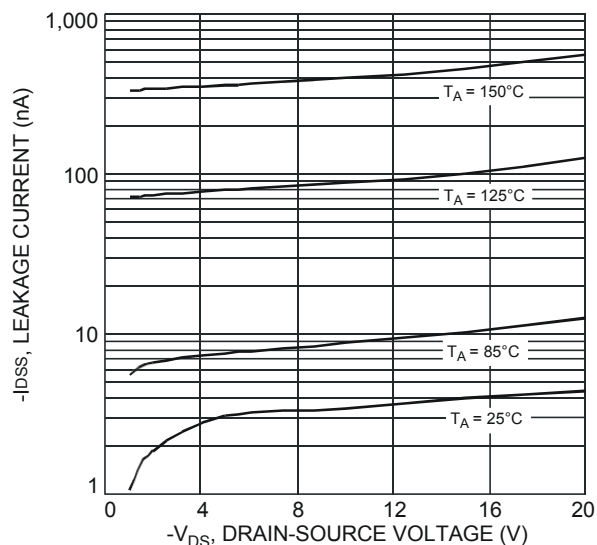


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

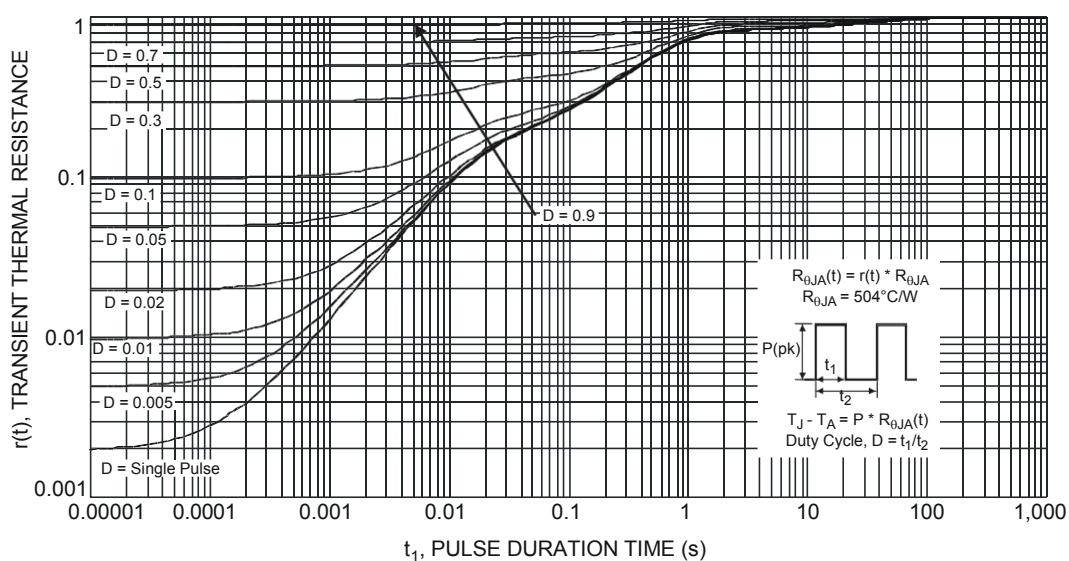


Fig. 11 Transient Thermal Response